

DMT3006LDV

DUAL 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UXC)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	$10m\Omega$ @ $V_{GS} = 10V$	25A
30 V	$14m\Omega @ V_{GS} = 4.5V$	20A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

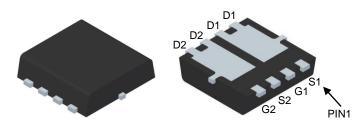
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

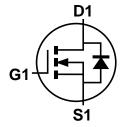
Mechanical Data

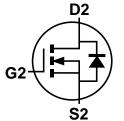
- Case: PowerDI[®]3333-8 (Type UXC)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (Type UXC)



Top View Bottom View





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3006LDV-7	PowerDI3333-8 (Type UXC)	2000/Tape & Reel
DMT3006LDV-13	PowerDI3333-8 (Type UXC)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3.Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	30	٧		
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 7) Steady $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$			I _D	25 20	А
Maximum Body Diode Forward Current (Note 7)	Is	25	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	90	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	90	Α
Avalanche Current (L = 0.1mH) (Note 8)			I _{AS}	34	Α
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	58	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_D	0.9	W
Thermal Pagistance, Junction to Ambient (Note 5)	Steady State	ם	134	°C/W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\Theta JA}$	78	C/VV
Total Power Dissipation (Note 6)		P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	C	70	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\Theta JA}$	41	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\Theta JC}$	14	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

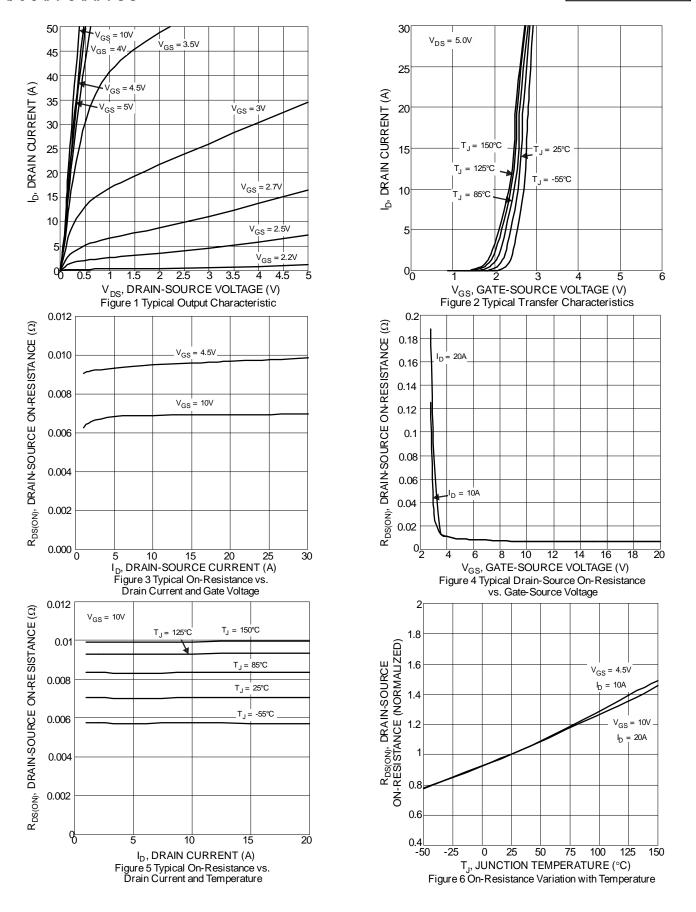
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			7.6	10	mΩ	$V_{GS} = 10V, I_D = 9.0A$	
Static Dialin-Source On-Resistance	R _{DS(ON)}		10.0	14	11122	$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	V_{SD}	_	0.70	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1,155			V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss		456		pF		
Reverse Transfer Capacitance	Crss	_	72	_		I = 1.0IVIH2	
Gate Resistance	R_G	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	8.4	_		V _{DD} = 15V, I _D = 9A	
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	16.7	_	nC		
Gate-Source Charge	Q_{GS}	_	2.2	_	iiC		
Gate-Drain Charge	Q_GD		3.5	_			
Turn-On Delay Time	t _{D(ON)}		3.5	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 9A$	
Turn-On Rise Time	t _R		5.5	_			
Turn-Off Delay Time	t _{D(OFF)}		13.5	_	ns		
Turn-Off Fall Time	t _F		4.6	_			
Reverse Recovery Time	t _{RR}		19.3	_	ns	1 4 5 4 3 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	
Reverse Recovery Charge	Q_{RR}	_	8.6	_	nC	$I_F = 1.5A$, di/dt = 100A/ μ s	

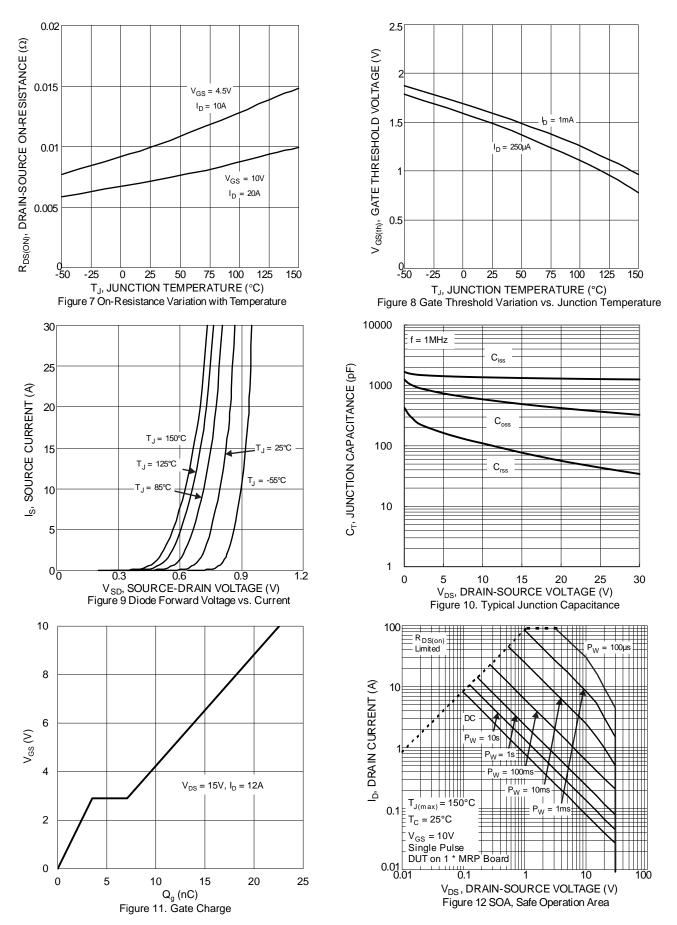
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_{J} = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

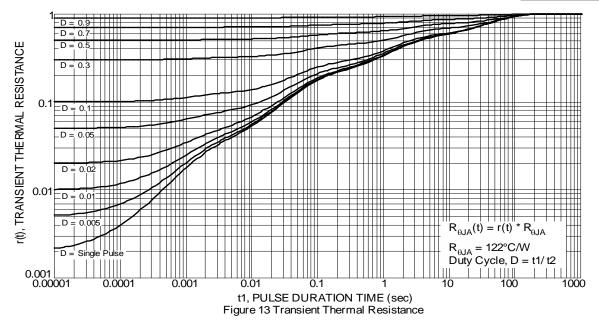








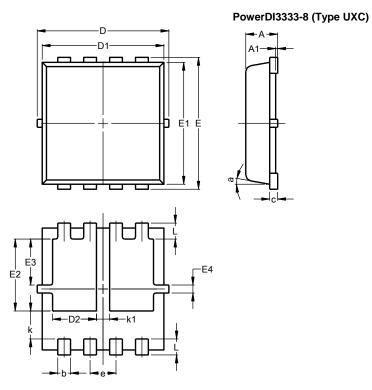






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

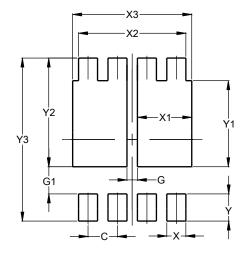


PowerDI3333-8						
(Type UXC)						
Dim	n Min Max Typ					
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
а	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.600
Х	0.420
X1	1.200
X2	2.370
Х3	2.630
Υ	0.600
Y1	1.900
Y2	2.400
Y3	3.600



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